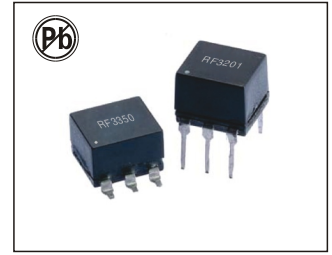


WIDEBAND RF IMPEDANCE MATCHING TRANSFORMERS

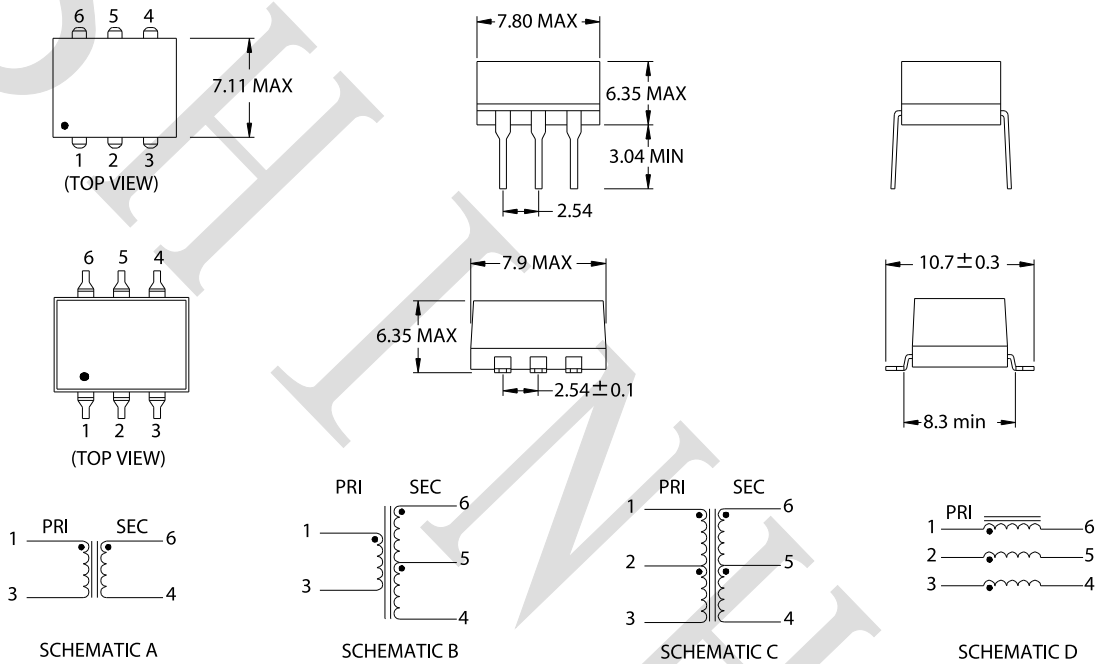
RF32 SERIES



FEATURES:

- Fully encapsulated
- Low leakage inductance, winding capacitance, and D.C. Resistance
- Low profile
- Low insertion loss
- Frequency range 10 kHz to 500 MHz
- Impedance levels from 12.5 Ω to 800 Ω (nominal 50 Ω)
- 6 pin DIP and SMD
- RoHS compliant

PHYSICAL CHARACTERISTICS & WINDING

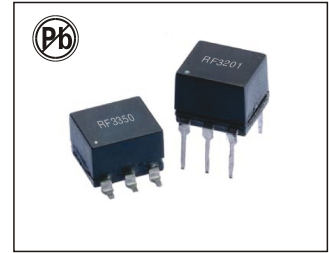


ELECTRICAL CHARACTERISTICS @ 25°C

Part Number	Turns ratio ± 5%	Pri inductance		Rise time us Max	Leakage inductance uH Max	Cw/w pF Max	DCR Ohms Max 20°C		Bandwidth for -3dB Loss MHz	Pri ET-Constant V-us Min	Schematic Figure
		uH Min	Pulse width us for 50% drop				N1	N2			
RF3201	1:1	80	2.20	2.2	0.15	12	0.20	0.20	0.05~110	2.5	A
RF3202	1ct:1ct	80	2.20	3.0	0.18	15	0.20	0.20	0.05~90	2.5	C
RF3203	1:1ct	80	2.20	3.0	0.18	15	0.20	0.20	0.05~90	2.5	B
RF3204	1:1:1	40	1.10	2.0	0.10	12	0.16	0.16	0.10~150	2.0	D
RF3205	1:2	40	1.10	3.0	0.14	15	0.20	0.30	0.10~110	2.0	A
RF3206	1:2ct	40	1.10	3.0	0.14	15	0.20	0.30	0.10~110	2.0	B
RF3207	1:1.414	80	2.20	4.0	0.30	18	0.20	0.30	0.05~50	2.5	A
RF3208	1:1.414ct	80	2.20	3.0	0.20	18	0.20	0.30	0.05~80	2.5	B
RF3209	1:4	20	0.55	6.0	0.10	10	0.20	0.60	0.20~60	1.25	A
RF3210	1:4ct	20	0.55	6.0	0.10	10	0.20	0.60	0.20~60	1.25	B
RF3211	1ct:1ct	20	2.20	3.0	0.20	15	0.30	0.30	0.05~90	2.5	C
RF3212	2ct:1ct	100	1.10	3.5	0.30	18	0.40	0.40	0.10~110	2.5	C

WIDEBAND RF IMPEDANCE MATCHING TRANSFORMERS

RF33 SERIES



FEATURES:

- Fully encapsulated
- Low leakage inductance, winding capacitance, and D.C. Resistance
- Low profile
- Low insertion loss
- Frequency range 10 kHz to 500 MHz
- Impedance levels from 12.5 Ω to 800 Ω (nominal 50 Ω)
- 6 pin DIP and SMD
- RoHS compliant

ELECTRICAL CHARACTERISTICS@25°C

Part Number	Impedance ratio	Frequency range(MHz)			Schematic Figure
		Insulation Loss 3dB	Insulation Loss 2dB	Insulation Loss 1dB	
RF3350	1:1	0.05~200	0.08~150	0.2~80	B
RF3351	1:1	0.003~300	0.01~150	0.02~50	B
RF3352	2:1	0.07~200	0.1~100	0.5~50	B
RF3353	2.5:1	0.01~100	0.02~50	0.05~20	B
RF3354	3:1	0.05~250	0.1~200	0.5~70	B
RF3355	4:1	0.2~350	0.35~300	2~100	B
RF3356	4:1	0.02~250	0.05~150	0.1~100	B
RF3357	5:1	0.3~300	0.6~200	0.5~100	B
RF3358	8:1	0.03~140	0.1~90	1~60	B
RF3359	13:1	0.3~120	0.7~80	5~20	B
RF3360	16:1	0.03~75	0.06~30	10~20	B
RF3361	1:1	0.15~400	0.35~200	2~50	A
RF3362	1:1	0.01~150	0.02~100	0.005~50	A
RF3363	1.5:1	0.1~300	0.2~150	0.5~80	A
RF3364	1.5:1	0.02~100	0.05~50	0.1~25	A
RF3365	2.5:1	0.01~100	0.02~50	0.05~20	A
RF3366	4:1	0.02~200	0.05~150	0.1~100	A
RF3367	9:1	0.15~200	0.3~150	2~40	A
RF3368	16:1	0.3~120	0.7~80	0.5~20	A
RF3369	36:1	0.03~20	0.05~10	0.1~5	A
RF3370	1:1	0.004~500	0.02~200	0.1~50	C
RF3371	1.5:1	0.075~500	0.2~100	0.1~50	C
RF3372	2.5:1	0.01~50	0.025~25	0.05~10	C
RF3373	4:1	0.05~200	0.2~50	1~30	C
RF3374	25:1	0.02~30	0.05~20	0.1~10	C

Note:

- Designed for use in 50 Ω wideband R.F. and fast rise time pulse applications
- Temperature Range: Operating: 0°C to +70°C
Storage: -25°C to +105°C
- High Potential Test-----200 Vrms
- Insulation Resistance -----10000 MΩ
- All specifications subject to change without notice.